

PATENT ABSTRACTS OF JAPAN

(11) Publication number : 2000-122295

(43) Date of publication of application : 28.04.2000

(51) Int.Cl.

G03F 7/039
C08F 20/28
C09D133/04
G03F 7/027
G03F 7/028
H01L 21/027
// C07C 69/54

(21) Application number : 11-135624

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(22) Date of filing : 17.05.1999

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(30) Priority

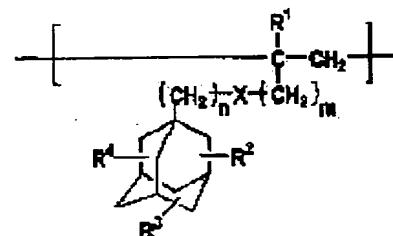
Priority number : 10143535 Priority date : 25.05.1998 Priority country : JP
10227336 11.08.1998 JP

(54) COMPOUND FOR PHOTORESIST AND RESIN COMPOSITION FOR PHOTORESIST

(57) Abstract:

PROBLEM TO BE SOLVED: To form a fine pattern by using a resin composition for a photoresist having high etching solution resistance and capable of being solubilized by photoirradiation.

SOLUTION: The resin composition for a photoresist comprises a polymer having an adamantane skeleton of the formula and a photo-acid generating agent. In the formula, R₁ is H or methyl, R₂-R₄ are mutually the same or different and are each H, a halogen, alkyl, hydroxyl, hydroxymethyl, carboxyl and a functional group which is released by an acid and forms hydroxyl, hydroxymethyl or carboxyl, at least one of R₂-R₄ is the functional group, X is an ester or amino bond and (m) and (n) are each 0 or 1.



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[Date of request for examination] 17.03.2006

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

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